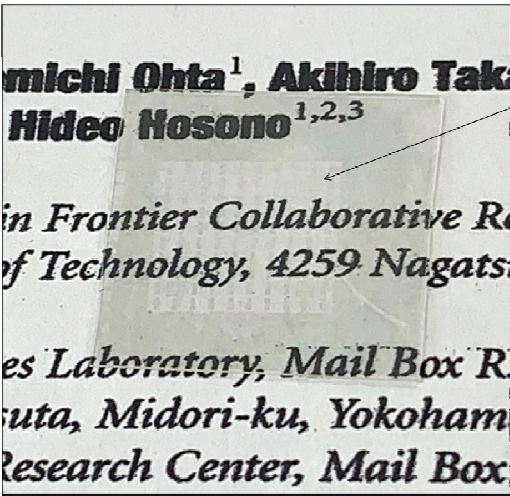
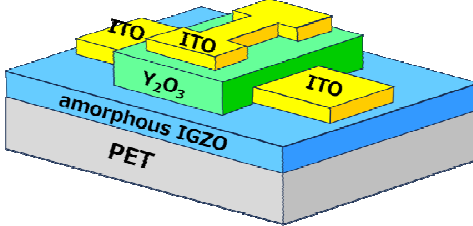


**The world's first amorphous oxide semiconductor thin-film transistor**

Registration No.	Number 00377		
Registration Date	September 10, 2024	Registration Category	Category 2

Name (Model, etc.)	Flexible and Transparent Amorphous IGZO Thin-Film Transistor		
Location	Yokohama-shi, Kanagawa		
	Tokyo Institute of Technology		
Owner (Custodian)	Tokyo Institute of Technology		
Manufacturer (Company)	Hosono & Kamiya Laboratory at Tokyo Institute of Technology, JST ERATO Project "HOSONO Transparent ElectroActive Materials", and JST ERATO-SORST Project "Function Cultivation of Transparent Oxides Utilizing Nano-Structure and Their Application"		
Year Manufactured	2004		
Year first appeared	2004		
Reason For Selection	This material is the world's first transparent amorphous oxide semiconductor In-Ga-Zn-O [IGZO] thin-film transistor (TFT), which has triggered a game-changing advancement in the flat-panel display market. This discovery and invention were published in <i>Nature</i> in 2004 [ <i>Nature</i> , 432, 488-492 (2004)] and opened up new markets for high-definition LCD and OLED TVs, which had been difficult to achieve with amorphous silicon TFTs. This technology has now spilled over into medical devices and semiconductor memory, and has caused innovation in the global electronics industry. This excellence in materials technology is of historic importance in the fields of materials science and semiconductor electronics.		
Registration Standard	1-C (Contributed to the creation of a new scientific or technological field.) 2-A (Played a notable role in improving people's way of life and creating new ways of living.)		

Open/Closed to Public	Closed to Public		
-----------------------	------------------	--	--

Photo	 <div data-bbox="917 1496 1401 1585" style="border: 1px solid black; padding: 5px;"> <p>It is known that many patterns are formed on transparent sheets due to the interference of light. In the pattern, a-IGZO thin-film transistors with the device structure shown below are formed.</p> </div> <div data-bbox="917 1608 1401 1937" style="text-align: center;"> <p><b>Image of "a-IGZO TFT" Structure</b></p>  <ul style="list-style-type: none"> <li>● amorphous IGZO layer : 30 nm</li> <li>● Y<sub>2</sub>O<sub>3</sub> gate dielectric layer : 140 nm</li> <li>● ITO electrode layer : 40 nm</li> </ul> <p><small>This figure was prepared by National Museum of Nature and Science, based on the figure in <i>Nature</i>, 432, 488-492 (2004).</small></p> </div>		
Other useful information			